



FEATURES

- Circular Active Area
- Ideal for Electron Detection
- High Speed
- Protective Cover Plate³

Electro-Optical Characteristics at 25°C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area	9 mm		63		mm ²
Responsivity	(see graphs on next page)				A/W
Reverse Breakdown Voltage, V _R	I _R = 1 μ A	160			Volts
Capacitance, C	V _R = 0 V		700	2000	pF
Rise Time	R _L = 50 Ω , V _R = 150 V			10	nsec
Dark Current	V _R = 150 V			100	nA

Thermal Parameters

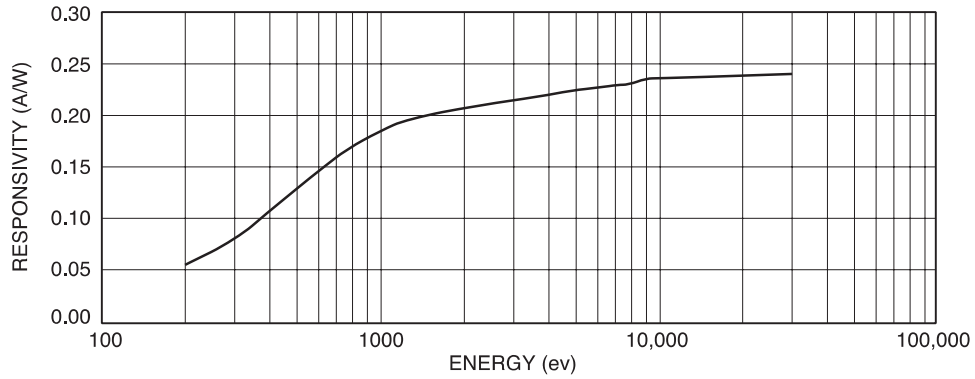
Storage and Operating Temperature Range	Units
Ambient ¹	-10°C to 40°C
Nitrogen or Vacuum	-20°C to 80°C
Lead Soldering Temperature ²	260°C

¹ Temperatures exceeding these parameters may create oxide growth on the active area. Over time responsivity to low energy radiation and wavelengths below 150 nm will be compromised.

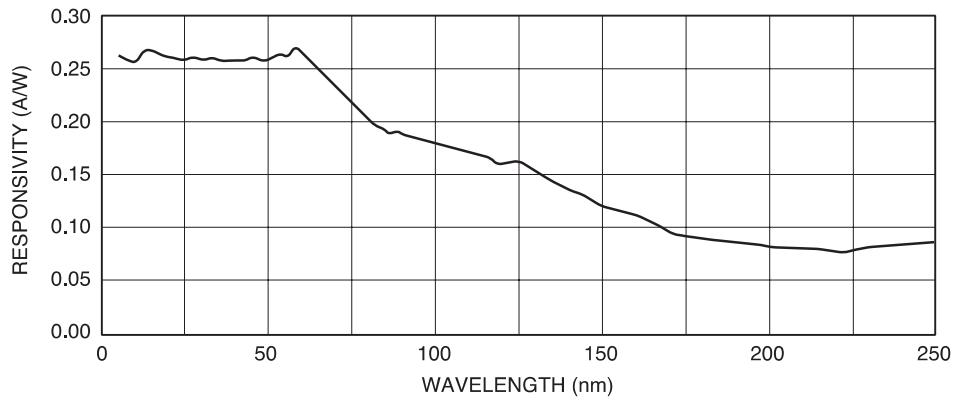
² 0.080" from case for 10 seconds.

³ Shipped with temporary cover to protect the photodiode array and wire bonds. Review the Application Note, "Handling Precautions for AXUV, SXUV, and UVG Detectors", prior to removing cover.

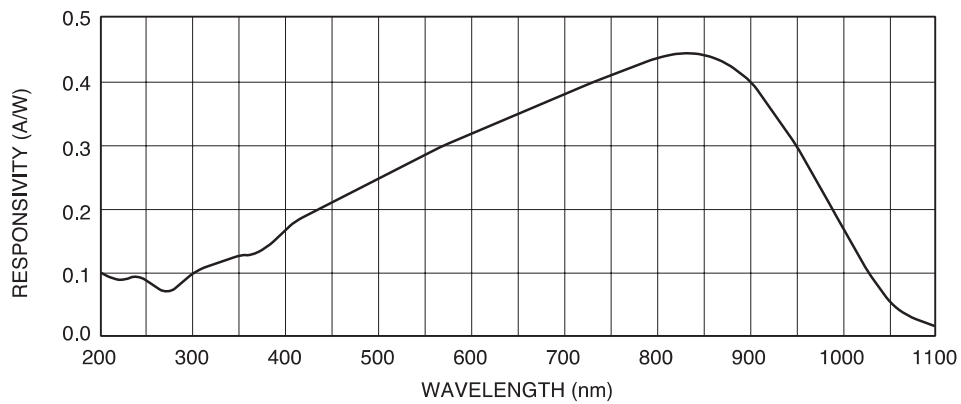
Typical Electron Response



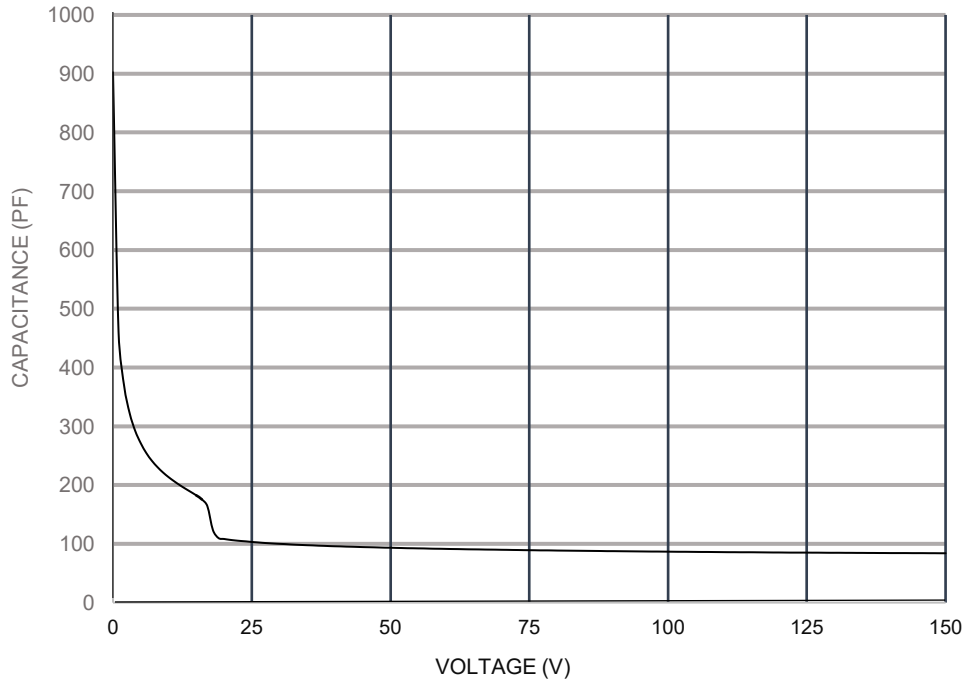
Typical EUV-UV Photon Response



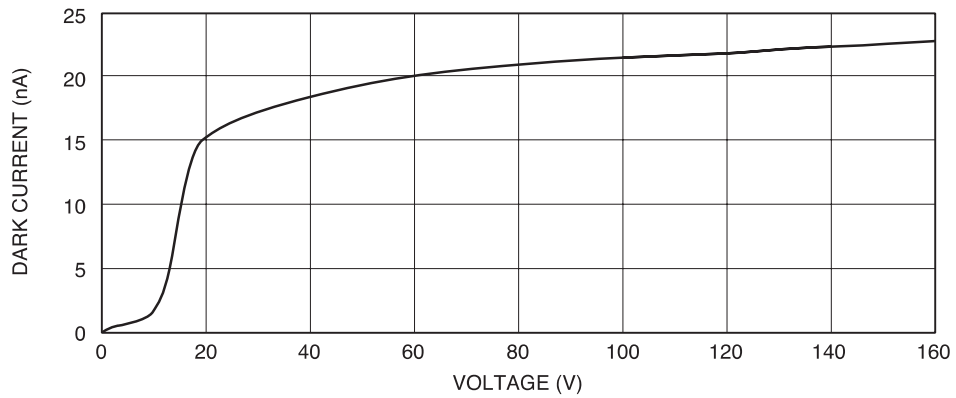
Typical UV-VIS-NIR Photon Responsivity



Capacitance vs. Voltage



Dark Current vs. Voltage



Package Information

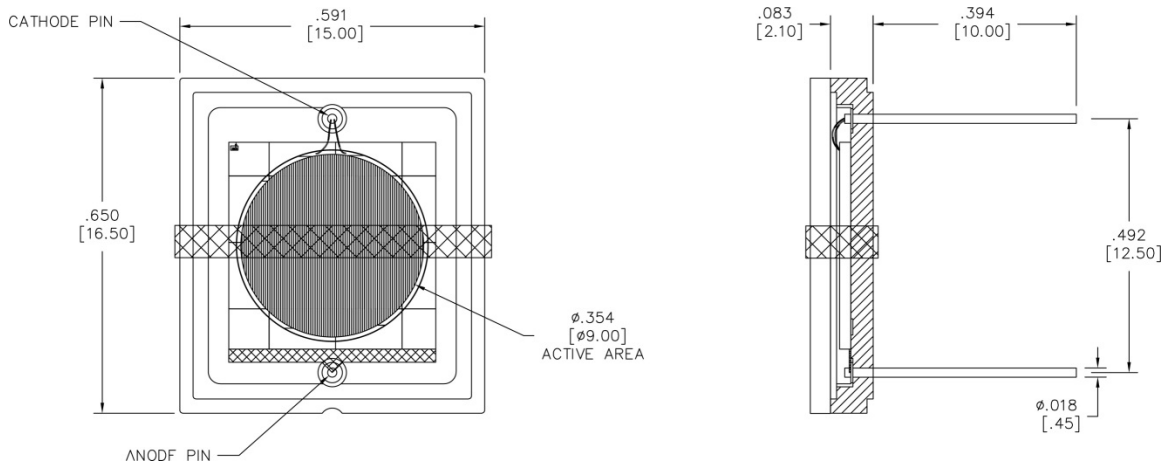


From Deep UV to Mid-IR

OPTO DIODE
An ITW Company

Photodiode $\Phi 9$ mm

AXUV63HS1



Dimensions are in inch [metric] units.

Specifications are subject to change without prior notice.

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